

Day : Thursday
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PALM INTRANET

Inventor Name Search Result

Your Search was:

Last Name = HSU

First Name = SHENG TENG

Application#	Patent#	Status	Date Filed	Title	Inventor Name 51
<u>10401203</u>	Not Issued	094	03/27/2003	SPIN TRANSISTOR MAGNETIC RANDOM ACCESS MEMORY DEVICE	HSU, SHENG TENG
<u>10306644</u>	Not Issued	041	11/26/2002	COMMON BIT/COMMON SOURCE LINE HIGH DENSITY 1T1R R-RAM ARRAY	HSU, SHENG TENG
<u>10140460</u>	<u>6716744</u>	150	05/06/2002	ULTRA THIN TUNGSTEN METAL FILMS USED AS ADHESION PROMOTER BETWEEN BARRIER METALS AND COPPER	HSU, SHENG TENG
<u>10002108</u>	<u>6524893</u>	150	12/05/2001	ELECTROSTATIC DISCHARGE PROTECTION DEVICE FOR SEMICONDUCTOR INTEGRATED CIRCUIT, METHOD FOR PRODUCING THE SAME, AND ELECTROSTATIC DISCHARGE PROTECTION CIRCUIT USING THE SAME	HSU, SHENG TENG
<u>09819879</u>	<u>6503763</u>	150	03/27/2001	METHOD OF MAKING MFMOS CAPACITORS WITH HIGH DIELECTRIC CONSTANT MATERIALS	HSU, SHENG TENG
<u>09481660</u>	Not Issued	161	01/12/2000	MOS TRANSISTOR WITH SHALLOW SOURCE/DRAIN JUNCTIONS AND LOW LEAKAGE CURRENT	HSU , SHENG TENG
<u>09455588</u>	<u>6218249</u>	150	12/06/1999	MOS TRANSISTOR HAVING SHALLOW SOURCE/DRAIN JUNCTIONS AND LOW LEAKAGE CURRENT	HSU , SHENG TENG
<u>09455262</u>	<u>6649963</u>	150	12/06/1999	FERROELECTRIC MEMORY CELL FOR VLSI RAM	HSU , SHENG TENG

<u>09351645</u>	<u>6204176</u>	150	07/12/1999	SUBSTITUTED PHENYLETHYLENE PRECURSOR DEPOSITION METHOD	HSU, SHENG TENG
<u>09330900</u>	<u>6506643</u>	150	06/11/1999	METHOD FOR FORMING A DAMASCENE FERAM CELL STRUCTURE	HSU , SHENG TENG
<u>09316661</u>	<u>6190963</u>	150	05/21/1999	COMPOSITE IRIDIUM-METAL-OXYGEN BARRIER STRUCTURE WITH REFRACTORY METAL COMPANION BARRIER AND METHOD FOR SAME	HSU , SHENG TENG
<u>09316646</u>	<u>6399521</u>	150	05/21/1999	COMPOSITE IRIDIUM BARRIER STRUCTURE WITH OXIDIZED REFRACTORY METAL COMPANION BARRIER AND METHOD FOR SAME	HSU , SHENG TENG
<u>09301435</u>	Not Issued	161	04/28/1999	MULTI-PHASE LEAD GERMANATE FILM AND DEPOSITION METHOD	HSU , SHENG TENG
<u>09301434</u>	<u>6590243</u>	150	04/28/1999	FERROELASTIC LEAD GERMANATE THIN FILM AND DEPOSITION METHOD	HSU , SHENG TENG
<u>09301420</u>	<u>6410343</u>	150	04/28/1999	C-AXIS ORIENTED LEAD GERMANATE FILM AND DEPOSITION METHOD	HSU , SHENG TENG
<u>09292064</u>	<u>6146904</u>	150	04/14/1999	METHOD OF MAKING A TWO TRANSISTOR FERROELECTRIC MEMORY CELL	HSU , SHENG TENG
<u>09291688</u>	<u>6242771</u>	150	04/13/1999	CHEMICAL VAPOR DEPOSITION OF PB ₅ GE ₃ O ₁₁ THIN FILM FOR FERROELECTRIC APPLICATIONS	HSU , SHENG TENG
<u>09287726</u>	<u>6117691</u>	150	04/07/1999	METHOD OF MAKING A SINGLE TRANSISTOR FERROELECTRIC MEMORY CELL WITH ASYMMETRICAL FERROELECTRIC POLARIZATION	HSU , SHENG TENG
<u>09281731</u>	<u>6015918</u>	150	03/30/1999	ALLYL-DERIVED PRECURSOR AND SYNTHESIS METHOD	HSU , SHENG TENG
<u>09281722</u>	<u>6090963</u>	150	03/30/1999	ALKENE LIGAND PRECURSOR AND SYNTHESIS METHOD	HSU , SHENG TENG
<u>09270901</u>	<u>6281589</u>	150	03/15/1999	SYSTEM FOR SELECTIVELY	HSU ,

				CLEANING COPPER SUBSTRATE SURFACES, IN-SITU, TO REMOVE COPPER OXIDES	SHENG TENG
<u>09263970</u>	<u>6236113</u>	150	03/05/1999	IRIDIUM COMPOSITE BARRIER STRUCTURE AND METHOD FOR SAME	HSU , SHENG TENG
<u>09263595</u>	Not Issued	161	03/05/1999	IRIDIUM CONDUCTIVE ELECTRODE/BARRIER STRUCTURE AND METHOD FOR SAME	HSU , SHENG TENG
<u>09257217</u>	<u>6388296</u>	150	02/25/1999	CMOS SELF-ALIGNED STRAPPED INTERCONNECT	HSU , SHENG TENG
<u>09248630</u>	<u>6140189</u>	150	02/11/1999	METHOD FOR FABRICATING A LOCOS MOS DEVICE FOR ESD PROTECTION	HSU , SHENG TENG
<u>09215921</u>	<u>5994571</u>	150	12/18/1998	SUBSTITUTED ETHYLENE PRECURSOR AND SYNTHESIS METHOD	HSU , SHENG TENG
<u>09210099</u>	<u>6245261</u>	150	12/11/1998	SUBSTITUTED PHENYLETHYLENE PRECURSOR AND SYNTHESIS METHOD	HSU , SHENG TENG
<u>09195392</u>	<u>6291325</u>	150	11/18/1998	ASYMMETRIC MOS CHANNEL STRUCTURE WITH DRAIN EXTENSION AND METHOD FOR SAME	HSU , SHENG TENG
<u>09193950</u>	Not Issued	161	11/18/1998	ASYMMETRIC CHANNEL DOPED MOS STRUCTURE	HSU , SHENG TENG
<u>09187238</u>	<u>6048740</u>	150	11/05/1998	FERROELECTRIC NONVOLATILE TRANSISTOR AND METHOD OF MAKING SAME	HSU , SHENG TENG
<u>09169084</u>	<u>6023102</u>	150	10/08/1998	LOW RESISTANCE CONTACT BETWEEN CIRCUIT METAL LEVELS	HSU , SHENG TENG
<u>09153379</u>	Not Issued	161	09/15/1998	CU(HFAC) TMVS PRECURSOR WITH WATER ADDITIVE TO INCREASE THE CONDUCTIVITY OF CU	HSU , SHENG TENG
<u>09135376</u>	<u>6002176</u>	150	08/17/1998	DIFFERENTIAL COPPER DEPOSITION ON INTEGRATED CIRCUIT SURFACES	HSU , SHENG TENG
<u>09113667</u>	<u>6368960</u>	150	07/10/1998	DOUBLE SIDEWALL RAISED SILICIDED SOURCE/DRAIN	HSU , SHENG

				CMOS TRANSISTOR TRENCH ISOLATION STRUCTURE AND METHOD FOR SAME	TENG HSU , SHENG TENG
<u>09047038</u>	<u>6169011</u>	150	03/24/1998	METHOD OF FORMING FULLY DEPLETED SIMOX CMOS HAVING ELECTROSTATIC DISCHARGE PROTECTION	HSU , SHENG TENG
<u>09031143</u>	<u>6114197</u>	150	02/26/1998	FABRICATION OF A PLANAR MOSFET WITH RAISED SOURCE/DRAIN BY CHEMICAL MECHANICAL POLISHING AND NITRIDE REPLACEMENT	HSU , SHENG TENG
<u>09028157</u>	<u>6133106</u>	150	02/23/1998	PARTIAL SILICIDATION METHOD TO FORM SHALLOW SOURCE/DRAIN JUNCTIONS	HSU , SHENG TENG
<u>09023383</u>	<u>6071782</u>	150	02/13/1998	NITRIDE OVERHANG STRUCTURES FOR THE SILICIDATION OF TRANSISTOR ELECTRODES WITH SHALLOW JUNCTION	HSU , SHENG TENG
<u>09004991</u>	<u>6274421</u>	150	01/09/1998	METHOD OF MAKING METAL GATE SUB-MICRON MOS TRANSISTOR	HSU , SHENG TENG
<u>09002364</u>	<u>6011285</u>	150	01/02/1998	C-AXIS ORIENTED THIN FILM FERROELECTRIC TRANSISTOR MEMORY CELL AND METHOD OF MAKING THE SAME	HSU , SHENG TENG
<u>08997098</u>	Not Issued	161	12/23/1997	MOS SNAPBACK DEVICE WITH DRAIN SPACER AND METHOD FOR SAME	HSU , SHENG TENG
<u>08984801</u>	<u>5910673</u>	150	12/04/1997	LOCOS MOS DEVICE FOR ESD PROTECTION	HSU , SHENG TENG
<u>08984789</u>	<u>5907762</u>	150	12/04/1997	METHOD OF MANUFACTURE OF SINGLE TRANSISTOR FERROELECTRIC MEMORY CELL USING CHEMICAL-MECHANICAL POLISHING	HSU , SHENG TENG
<u>08943299</u>	Not Issued	161	10/14/1997	DIRECTIONALLY DEPOSITED SILICIDE ON TRANSISTOR ELECTRODES AND METHOD FOR SAME	HSU , SHENG TENG
<u>08919398</u>	Not Issued	161	08/28/1997	GE-SI SOI MOS TRANSISTOR AND METHOD OF FABRICATING SAME	HSU , SHENG TENG

08918678	5891782	150	08/21/1997	A METHOD FOR FABRICATING ASYMMETRIC CHANNEL DOPED STRUCTURE	HSU , SHENG TENG
08905380	5962884	150	08/04/1997	SINGLE TRANSISTOR FERROELECTRIC MEMORY CELL WITH ASYMMETRICAL FERROELECTRIC POLARIZATION AND METHOD OF MAKING THE SAME	HSU , SHENG TENG
08845982	Not Issued	161	05/01/1997	RAISED SOURCE/DRAIN MOS TRANSISTOR WITH COVERED EPITAXIAL NOTCHES AND FABRICATION METHOD	HSU , SHENG TENG
08812579	5731608	150	03/07/1997	ONE TRANSISTOR FERROELECTRIC MEMORY CELL AND METHOD OF MAKING THE SAME	HSU , SHENG TENG
08708683	5677214	150	09/05/1996	RAISED SOURCE/DRAIN MOS TRANSISTOR WITH COVERED EPITAXIAL NOTCHES AND FABRICATION METHOD	HSU , SHENG TENG

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Inventor Name Search Result

Your Search was:

Last Name = HSU

First Name = SHENG TENG

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>60107892</u>	<u>Not Issued</u>	159	11/10/1998	IMPROVED COPPER PRECURSOR AND SYNTHESIS METHOD	HSU , SHENG TENG
<u>09481674</u>	<u>6462366</u>	150	01/12/2000	FERROELECTRIC NONVOLATILE TRANSISTOR	HSU , SHENG TENG
<u>09379108</u>	<u>6338986</u>	150	08/23/1999	ELECTROSTATIC DISCHARGE PROTECTION DEVICE FOR SEMICONDUCTOR METHOD, FOR PRODUCING THE SAME AND ELECTROSTATIC DISCHARGE PROTECTION CIRCUIT USING THE SAME	HSU , SHENG TENG
<u>09378653</u>	<u>6339245</u>	150	08/20/1999	NITRIDE OVERHANG STRUCTURE FOR THE SILICIDATION OF TRANSISTOR ELECTRODES WITH SHALLOW JUNCTIONS	HSU , SHENG TENG
<u>09363245</u>	<u>Not Issued</u>	161	07/28/1999	SINGLE PHASE PEROVSKITE FERROELECTRIC FILM ON PLATINUM AND METHOD FOR FORMING SAME	HSU , SHENG TENG
<u>09352458</u>	<u>6346978</u>	150	07/13/1999	SOI TFT ARRAY SUBSTRATE FOR LCD PROJECTION DISPLAY	HSU , SHENG TENG
<u>09317780</u>	<u>6420740</u>	150	05/24/1999	LEAD GERMANATE FERROELECTRIC STRUCTURE WITH MULTI-LAYERED ELECTRODE	HSU , SHENG TENG
<u>09302272</u>	<u>6190925</u>	150	04/28/1999	EPITAXIALLY GROWN LEAD GERMANATE FILM AND DEPOSITION METHOD	HSU , SHENG TENG
<u>09301435</u>	<u>Not Issued</u>	161	04/28/1999	MULTI-PHASE LEAD GERMANATE FILM AND DEPOSITION METHOD	HSU , SHENG TENG

<u>09090802</u>	<u>5915199</u>	150	06/04/1998	METHOD FOR MANUFACTURING A CMOS SELF- ALIGNED STRAPPED INTERCONNECTION	HSU , SHENG TENG
<u>09088456</u>	<u>6184157</u>	150	06/01/1998	STRESS-LOADED FILM AND METHOD FOR SAME	HSU , SHENG TENG
<u>09082084</u>	<u>6080612</u>	150	05/20/1998	A METHOD OF FORMING AN ULTRA-THIN SOI ELECTROSTATIC DISCHARGE PROTECTION DEVICE	HSU , SHENG TENG
<u>08896114</u>	<u>5904565</u>	150	07/17/1997	LOW RESISTANCE CONTACT BETWEEN INTEGRATED CIRCUIT METAL LEVELS AND METHOD FOR SAME	HSU , SHENG TENG
<u>08870375</u>	<u>6048738</u>	150	06/06/1997	METHOD OF MAKING FERROELECTRIC MEMORY CELL FOR VLSI RAM	HSU , SHENG TENG
<u>08869534</u>	<u>5942776</u>	150	06/06/1997	SHALLOW JUNCTION FERROELECTRIC MEMORY CELL AND METHOD OF MAKING THE SAME	HSU , SHENG TENG
<u>08861808</u>	<u>5939334</u>	150	05/22/1997	SYSTEM AND METHOD OF SELECTIVELY CLEANING COPPER SUBSTRATE SURFACES, IN-SITU, TO REMOVE COPPER OXIDES	HSU , SHENG TENG
<u>08847916</u>	<u>5932913</u>	150	04/28/1997	MOS TRANSISTOR WITH CONTROLLED SHALLOW SOURCE/DRAIN JUNCTION, SOURCE/ DRAIN STRAP PORTIONS, AND SOURCE/DRAIN ELECTRODES ON FIELD INSULATION LAYERS	HSU , SHENG TENG
<u>08834499</u>	<u>6018171</u>	150	04/04/1997	SHALLOW JUNCTION FERROELECTRIC MEMORY CELL HAVING A LATERALLY EXTENDING P-N JUNCTION AND METHOD OF MAKING THE SAME	HSU , SHENG TENG
<u>06018859</u>	<u>4247861</u>	150	03/09/1979	HIGH PERFORMANCE ELECTRICALLY ALTERABLE READ-ONLY MEMORY (EAROM)	HSU , SHENG TENG
<u>06015247</u>	<u>4249095</u>	150	02/26/1979	COMPARATOR, SENSE AMPLIFIER	HSU , SHENG TENG
<u>06012808</u>	Not Issued	161	02/16/1979	METHOD OF ENHANCING	HSU , SHENG

				DIELECTRIC STRENGTH BY ION IMPLANTATION	TENG
05959848	4232327	150	11/13/1978	EXTENDED DRAIN SELF-ALIGNED SILICON GATE MOSFET	HSU , SHENG TENG
05873593	4178605	150	01/30/1978	COMPLEMENTARY MOS INVERTER STRUCTURE	HSU , SHENG TENG
05864766	4162504	150	12/27/1977	FLOATING GATE SOLID-STATE STORAGE DEVICE	HSU , SHENG TENG

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Inventor Name Search Result

Your Search was:

Last Name = LI

First Name = TINGKAI

Application#	Patent#	Status	Date Filed	Title	Inventor Name 51
<u>10741803</u>	Not Issued	020	12/18/2003	INDIUM OXIDE CONDUCTIVE FILM	LI, TINGKAI
<u>10730584</u>	Not Issued	020	12/08/2003	RRAM MEMORY CELL ELECTRODES	LI, TINGKAI
<u>10677007</u>	Not Issued	030	09/30/2003	MOCVD SELECTIVE DEPOSITION OF C-AXIS ORIENTED PB5GE3O11 THIN FILMS ON IN2O3 OXIDES	LI, TINGKAI
<u>10676983</u>	Not Issued	020	09/30/2003	SELECTIVE ETCHING PROCESSES FOR IN2O3 THIN FILMS IN FERAM DEVICE APPLICATIONS	LI, TINGKAI
<u>10659547</u>	Not Issued	030	09/09/2003	CONDUCTIVE METAL OXIDE GATE FERROELECTRIC MEMORY TRANSISTOR	LI, TINGKAI
<u>10640770</u>	Not Issued	020	08/13/2003	METHOD FOR OBTAINING REVERSIBLE RESISTANCE SWITCHES ON A PCMO THIN FILM WHEN INTEGRATED WITH A HIGHLY CRYSTALLIZED SEED LAYER	LI, TINGKAI
<u>10621863</u>	Not Issued	041	07/16/2003	MOCVD OF TIO2 THIN FILM FOR USE AS FERAM H2 PASSIVATION LAYER	LI, TINGKAI
<u>10606057</u>	Not Issued	030	06/25/2003	MOCVD SELECTIVE DEPOSITION OF C-AXIS ORIENTED PB5GE3O11 THIN FILMS ON HIGH-K GATE OXIDES	LI, TINGKAI
<u>10453831</u>	Not Issued	030	06/02/2003	METHOD OF FORMING FERROELECTRIC THIN FILMS ON A HIGH-K LAYER	LI, TINGKAI
<u>10442627</u>	Not Issued	030	05/21/2003	ASYMMETRIC MEMORY	LI, TINGKAI

CELL					
<u>10412890</u>	Not Issued	094	04/14/2003	FERROELASTIC INTEGRATED CIRCUIT DEVICE	LI, TINGKAI
<u>10409768</u>	Not Issued	061	04/09/2003	ALUMINUM TOP ELECTRODE FOR PGO THIN FILM APPLICATION	LI, TINGKAI
<u>10401212</u>	Not Issued	030	03/27/2003	SELECTIVELY DEPOSITED PGO THIN FILM METHOD FOR FORMING SAME	LI, TINGKAI
<u>10395368</u>	Not Issued	092	03/24/2003	METHOD OF FABRICATING NON-VOLATILE FERROELECTRIC TRANSISTORS	LI, TINGKAI
<u>10391294</u>	Not Issued	030	03/17/2003	METHOD OF ETCHING A SIN/IR/TAN OR SIN/IR/TI STACK USING AN ALUMINUM HARD MASK	LI, TINGKAI
<u>10385038</u>	<u>6703655</u>	150	03/10/2003	FERROELECTRIC MEMORY TRANSISTOR	LI, TINGKAI
<u>10377244</u>	Not Issued	041	02/27/2003	PRECURSOR SOLUTION AND METHOD FOR CONTROLLING THE COMPOSITION OF MOCVD DEPOSITED PCMO	LI, TINGKAI
<u>10345726</u>	Not Issued	041	01/15/2003	FERROELECTRIC RESISTOR NON-VOLATILE MEMORY ARRAY	LI, TINGKAI
<u>10345725</u>	<u>6649957</u>	150	01/15/2003	THIN FILM POLYCRYSTALLINE MEMORY STRUCTURE	LI, TINGKAI
<u>10319314</u>	<u>6716645</u>	150	12/12/2002	MFMOS CAPACITORS WITH HIGH DIELECTRIC CONSTANT MATERIALS	LI, TINGKAI
<u>10305551</u>	Not Issued	041	11/26/2002	FERROELECTRIC RESISTOR NON-VOLATILE MEMORY	LI, TINGKAI
<u>10282533</u>	Not Issued	061	10/28/2002	MFOS MEMORY TRANSISTOR	LI, TINGKAI
<u>10229603</u>	Not Issued	071	08/27/2002	ELECTRODE MATERIALS WITH IMPROVED HYDROGEN DEGRADATION RESISTANCE	LI, TINGKAI
<u>10196503</u>	Not Issued	094	07/15/2002	DEPOSITION METHOD FOR LEAD GERMANATE FERROELECTRIC STRUCTURE WITH MULTI-LAYERED	LI, TINGKAI

ELECTRODE					
<u>10164785</u>	<u>6531325</u>	150	06/04/2002	MEMORY TRANSISTOR AND METHOD OF FABRICATING SAME	LI, TINGKAI
<u>10099186</u>	<u>6534326</u>	150	03/13/2002	METHOD OF MINIMIZING LEAKAGE CURRENT & IMPROVING BREAKDOWN VOLTAGE OF POLYCRYSTALLINE MEMORY THIN FILMS	LI, TINGKAI
<u>10062336</u>	Not Issued	041	01/31/2002	METHOD TO FORM THICK RELAXED SIGE LAYER WITH TRENCH STRUCTURE	LI, TINGKAI
<u>10020868</u>	<u>6664116</u>	150	12/12/2001	SEED LAYER PROCESSES FOR MOCVD OF FERROELECTRIC THIN FILMS ON HIGH-K GATE OXIDES	LI, TINGKAI
<u>10015817</u>	Not Issued	161	10/30/2001	HIGH-K GATE OXIDES WITH BUFFER LAYERS OF TITANIUM FOR MFOS SINGLE TRANSISTOR MEMORY APPLICATIONS	LI, TINGKAI
<u>10010186</u>	<u>6410346</u>	150	12/06/2001	METHOD OF FORMING FERROELASTIC LEAD GERMANATE THIN FILMS	LI, TINGKAI
<u>09978487</u>	<u>6673664</u>	150	10/16/2001	METHOD OF MAKING A SELF-ALIGNED FERROELECTRIC MEMORY TRANSISTOR	LI, TINGKAI
<u>09965581</u>	<u>6457479</u>	150	09/26/2001	METHOD OF METAL OXIDE THIN FILM CLEANING	LI, TINGKAI
<u>09942205</u>	<u>6483137</u>	150	08/29/2001	CAPACITOR UTILIZING C-AXIS ORIENTED LEAD GERMANATE FILM	LI, TINGKAI
<u>09942203</u>	<u>6616857</u>	150	08/29/2001	C-AXIS ORIENTED LEAD GERMANATE FILM	LI, TINGKAI
<u>09929711</u>	<u>6475813</u>	150	08/13/2001	MOCVD AND ANNEALING PROCESSES FOR C-AXIS ORIENTED FERROELECTRIC THIN FILMS	LI, TINGKAI
<u>09929710</u>	<u>6566148</u>	150	08/13/2001	METHOD OF MAKING A FERROELECTRIC MEMORY TRANSISTOR	LI, TINGKAI
<u>09820039</u>	<u>6531324</u>	150	03/28/2001	MFOS MEMORY TRANSISTOR & METHOD OF FABRICATING SAME	LI, TINGKAI

<u>09819879</u>	<u>6503763</u>	150	03/27/2001	METHOD OF MAKING MFMOS CAPACITORS WITH HIGH DIELECTRIC CONSTANT MATERIALS	LI, TINGKAI
<u>09817712</u>	<u>6440752</u>	150	03/26/2001	ELECTRODE MATERIALS WITH IMPROVED HYDROGEN DEGRADATION RESISTANCE AND FABRICATION METHOD	LI, TINGKAI
<u>09814273</u>	<u>6495378</u>	150	03/21/2001	FERROELASTIC LEAD GERMANATE THIN FILM AND DEPOSITION METHOD	LI, TINGKAI
<u>09783815</u>	Not Issued	161	02/13/2001	MFMOS/MFMS NON-VOLATILE MEMORY TRANSISTORS AND METHOD OF MAKING SAME	LI, TINGKAI
<u>09704496</u>	<u>6281022</u>	150	11/01/2000	MULTI-PHASE LEAD GERMANATE FILM DEPOSITION METHOD	LI, TINGKAI
<u>09676719</u>	Not Issued	161	09/28/2000	EPITAXIALLY GROWN LEAD GERMANATE FILM	LI, TINGKAI
<u>09649381</u>	<u>6503314</u>	150	08/28/2000	MOCVD FERROELECTRIC AND DIELECTRIC THIN FILMS DEPOSITIONS USING MIXED SOLVENTS	LI, TINGKAI
<u>09588940</u>	<u>6303502</u>	150	06/06/2000	MOCVD METAL OXIDE FOR ONE TRANSISTOR MEMORY	LI, TINGKAI
<u>09489857</u>	Not Issued	161	01/24/2000	METHOD AND SYSTEM FOR METALORGANIC CHEMICAL VAPOR DEPOSITION (MOCVD) AND ANNEALING OF LEAD GERMANITE (PGO) THIN FILMS	LI, TINGKAI
<u>09481674</u>	<u>6462366</u>	150	01/12/2000	FERROELECTRIC NONVOLATILE TRANSISTOR	LI , TINGKAI
<u>09301434</u>	<u>6590243</u>	150	04/28/1999	FERROELASTIC LEAD GERMANATE THIN FILM AND DEPOSITION METHOD	LI , TINGKAI
<u>09187238</u>	<u>6048740</u>	150	11/05/1998	FERROELECTRIC NONVOLATILE TRANSISTOR AND METHOD OF MAKING SAME	LI , TINGKAI
<u>08454029</u>	<u>5527567</u>	150	05/30/1995	METALORGANIC CHEMICAL VAPOR DEPOSITION OF LAYERED STRUCTURE OXIDES	LI , TINGKAI

07533143	5102836	150	06/06/1990	CERAMIC MATERIALS WITH LOW THERMAL CONDUCTIVITY AND LOW COEFFICIENTS OF THERMAL EXPANSION	LI , TINGKAI
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Last Name = LI

First Name = TINGKAI

Application#	Patent#	Status	Date Filed	Title	Inventor Name 9
<u>09363245</u>	<u>Not Issued</u>	161	07/28/1999	SINGLE PHASE PEROVSKITE FERROELECTRIC FILM ON PLATINUM AND METHOD FOR FORMING SAME	LI , TINGKAI
<u>09317780</u>	<u>6420740</u>	150	05/24/1999	LEAD GERMANATE FERROELECTRIC STRUCTURE WITH MULTI-LAYERED ELECTRODE	LI , TINGKAI
<u>09302272</u>	<u>6190925</u>	150	04/28/1999	EPITAXIALLY GROWN LEAD GERMANATE FILM AND DEPOSITION METHOD	LI , TINGKAI
<u>09301435</u>	<u>Not Issued</u>	161	04/28/1999	MULTI-PHASE LEAD GERMANATE FILM AND DEPOSITION METHOD	LI , TINGKAI
<u>09301434</u>	<u>6590243</u>	150	04/28/1999	FERROELASTIC LEAD GERMANATE THIN FILM AND DEPOSITION METHOD	LI , TINGKAI
<u>09301420</u>	<u>6410343</u>	150	04/28/1999	C-AXIS ORIENTED LEAD GERMANATE FILM AND DEPOSITION METHOD	LI , TINGKAI
<u>09146224</u>	<u>6080241</u>	150	09/02/1998	CHEMICAL VAPOR DEPOSITION CHAMBER HAVING AN ADJUSTABLE FLOW FLANGE	LI , TINGKAI
<u>08325902</u>	<u>Not Issued</u>	161	10/19/1994	ALUMINA-SILICA ULTRAFILTRATION MEMBRANES	LI , TINGKAI K.
<u>08042611</u>	<u>5268199</u>	250	04/02/1993	ALKALI CORROSION RESISTANT COATINGS AND CERAMIC FOAMS HAVING SUPERFINE OPEN CELL STRUCTURE AND METHOD OF PROCESSING	LI , TINGKAI

	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	237	ferroelectric adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/13 12:55
2	BRS	56	("6069381" "5812442" "5303182" "5731608" "5962884" "6117691" "6018171" "5942776" "5932904" "6146904" "6011285" "6531325" "6538273" "3832700" "5365094" "5621681" "5744374" "6225655" "6362499" "6420742" "6498363" "6503763" "6151240" "5293510" "5383088" "5777356" "5798903" "6140173" "6214724") .pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/01 19:29
3	BRS	49	ferroelectric and (("6069381" "5812442" "5303182" "5731608" "5962884" "6117691" "6018171" "5942776" "5932904" "6146904" "6011285" "6531325" "6538273" "3832700" "5365094" "5621681" "5744374" "6225655" "6362499" "6420742" "6498363" "6503763" "6151240" "5293510" "5383088" "5777356" "5798903" "6140173" "6214724") .pn.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/01 19:59
4	BRS	1205	438/3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/01 19:55
5	BRS	965	438/585.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/01 19:56
6	BRS	729	438/197.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/01 19:57
7	BRS	181	438/142.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/01 19:59
8	BRS	849	438/287.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/01 19:59
9	BRS	42	ferroelectric and 438/287.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/01 20:00
10	BRS	30	ferroelectric adj transistor and 438/3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/01 20:00
11	BRS	14	ferroelectric adj transistor and sacrific\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/13 15:02
12	BRS	0	6531324.URPN.	USPAT	2004/05/13 13:07

	Type	Hits	Search Text	DBs	Time Stamp
13	BRS	9	("5510651" "5638319" "6048740" "6054355" "6072221" "6194752" "6251763" "6278164" "6303502") .PN.	USPAT	2004/05/13 13:12
14	BRS	1024	ferroelectric and sacrific\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/13 13:08
15	BRS	324	ferroelectric and sacrific\$3 and memory and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/13 13:09
16	BRS	282	ferroelectric and sacrific\$3 and memory and gate and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/13 13:09
17	BRS	22	ferroelectric and (sacrific\$3 adj3 gate) and memory and gate and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/13 13:09
18	BRS	73	ferroelectric adj transistor and (oxide with (Mo W Tc Re Tu Os Rh Ir Pd Pt In Zn Sn Nd Nb Sm La V))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/13 14:13
19	BRS	35	ferroelectric adj transistor and (oxide with (Mo W Tc Re Tu Os Rh Ir Pd Pt Zn Sn Nd Nb Sm La V))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/13 14:13
20	BRS	2	6274421.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/13 14:26
21	BRS	2	ferroelectric adj transistor and dummy adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/13 15:02